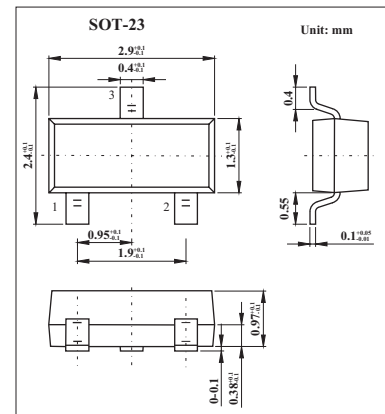


## Silicon Schottky Barrier Diode

## HRW0203A

## ■ Features

- Low forward voltage drop and suitable for high efficiency rectifying.
- MPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

| Parameter                                 | Symbol             | Value        | Unit             |
|---|--------------------|--------------|------------------|
| Repetitive peak reverse voltage           | $V_{RRM}$          | 20           | V                |
| Average rectified current                 | $I_o$              | 200          | mA               |
| Non-repetitive peak forward surge current | $I_{FSM}$ (Note 1) | 2            | A                |
| Junction temperature                      | $T_j$              | 125          | $^\circ\text{C}$ |
| Storage temperature                       | $T_{stg}$          | -55 to + 125 | $^\circ\text{C}$ |

Note

1. 50 Hz sine wave 1 Pulse

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

| Parameter       | Symbol | Conditions                           | Min | Typ | Max  | Unit               |
|-----------------|--------|--------------------------------------|-----|-----|------|--------------------|
| Forward voltage | $V_F$  | $I_F = 200\text{ mA}$                |     |     | 0.50 | V                  |
| Reverse current | $I_R$  | $V_R = 30\text{ V}$                  |     |     | 50   | $\mu\text{ A}$     |
| Capacitance     | $C$    | $V_R = 0\text{ V}, f = 1\text{ MHz}$ |     | 40  |      | $^\circ\text{C/W}$ |

## ■ Marking

|         |    |
|---------|----|
| Marking | S5 |
|---------|----|